

# 100V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI8080-5

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>C</sub> = +25°C
100V	1.5mΩ @ V <sub>GS</sub> = 10V	352A

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Engine management systems
- · Body control electronics
- DC-DC converters

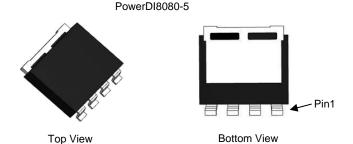
#### **Features and Benefits**

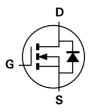
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production
   Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low Rds(ON) Minimizes Power Losses
- Wettable Flank for Improved Optical Inspection
- Fast Switching Speed
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH10H1M7SPGWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

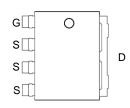
#### **Mechanical Data**

- Package: PowerDI<sup>®</sup>8080-5
- Package Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 63
- Weight: 0.36 grams (Approximate)





Internal Schematic



Top View
Pin Configuration

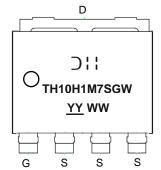
#### Ordering Information (Note 4)

Orderable Part Number	Package	Packing		
Orderable Part Number	Fackage	Qty.	Carrier	
DMTH10H1M7SPGWQ-13	PowerDI8080-5	2,000	Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



☐ → H = Manufacturer's Marking

TH10H1M7SGW = Product Type Marking Code

YYWW = Date Code Marking

YY = Year (ex: 25 = 2025)

WW = Week (01 to 53)

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# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		$V_{DSS}$	100	V
Gate-Source Voltage		Vgss	±20	V
Continuous Drain Current (Note 6)	Tc = +25°C Tc = +100°C	I <sub>D</sub>	352 249	А
Maximum Continuous Body Diode Forward Current (Note 6)		Is	352	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	1400	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I <sub>SM</sub>	1400	Α
Avalanche Current, L = 1mH		las	53	Α
Avalanche Energy, L = 1mH		E <sub>AS</sub>	1404	mJ

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	5	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	30	°C/W
Total Power Dissipation (Note 6)	Tc = +25°C	PD	405	W
Thermal Resistance, Junction to Case (Note 6)		R <sub>θ</sub> JC	0.37	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Cumbal	Min	Turn	May	l lmi4	Test Condition	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	T 5)./	400	1			T., 21 4 4	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	_	_	V	$V_{GS} = 0$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS		_	1	μΑ	$V_{DS} = 80V$ , $V_{GS} = 0$	
Gate-Source Leakage	I <sub>GSS</sub>		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(TH)	2	_	4	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>		1.13	1.5	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 25A	
Diode Forward Voltage	VsD		0.75	1.2	V	V <sub>G</sub> S = 0, I <sub>S</sub> = 20A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		10881			$V_{DS} = 50V, V_{GS} = 0,$ f = 1MHz	
Output Capacitance	Coss	_	3693	_	pF		
Reverse Transfer Capacitance	Crss		101	_			
Gate Resistance	Rg	-	0.71	_	Ω	$V_{DS} = 0$ , $V_{GS} = 0$ , $f = 1MHz$	
Total Gate Charge	Qg		171	_		V <sub>DD</sub> = 50V, I <sub>D</sub> = 25A, V <sub>GS</sub> = 10V	
Gate-Source Charge	Qgs		51	_	nC		
Gate-Drain Charge	$Q_{gd}$	-	40	_		VGS = 10V	
Turn-On Delay Time	tD(ON)	_	28	_		$V_{DD} = 50V, V_{GS} = 10V,$ $I_{D} = 25A, R_{G} = 3\Omega$	
Turn-On Rise Time	t <sub>R</sub>	-	43	_	no		
Turn-Off Delay Time	t <sub>D(OFF)</sub>		71	_	ns		
Turn-Off Fall Time	tF		54	_			
Body Diode Reverse-Recovery Time	t <sub>RR</sub>	_	99	_	ns	I= 254 di/dt 1004/vo	
Body Diode Reverse-Recovery Charge	$Q_{RR}$	_	334	_	nC	-  I <sub>F</sub> = 25A, di/dt = 100A/μs	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

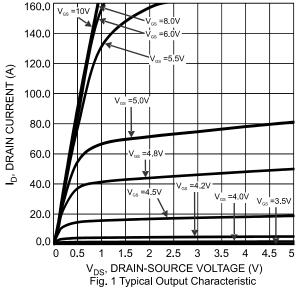
<sup>6.</sup> Thermal resistance from junction to soldering point (on the exposed drain pad).

<sup>7.</sup> Short duration pulse test used to minimize self-heating effect.

<sup>8.</sup> Guaranteed by design. Not subject to product testing.







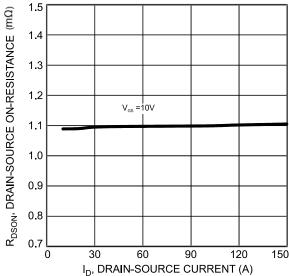


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

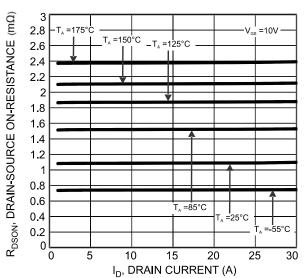
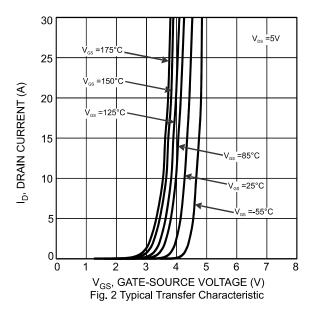
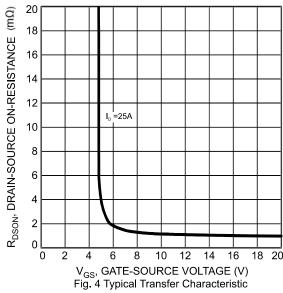


Fig. 5 Typical On-Resistance vs. Drain Current and Temperature





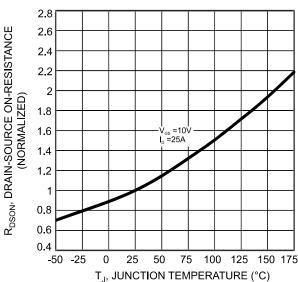
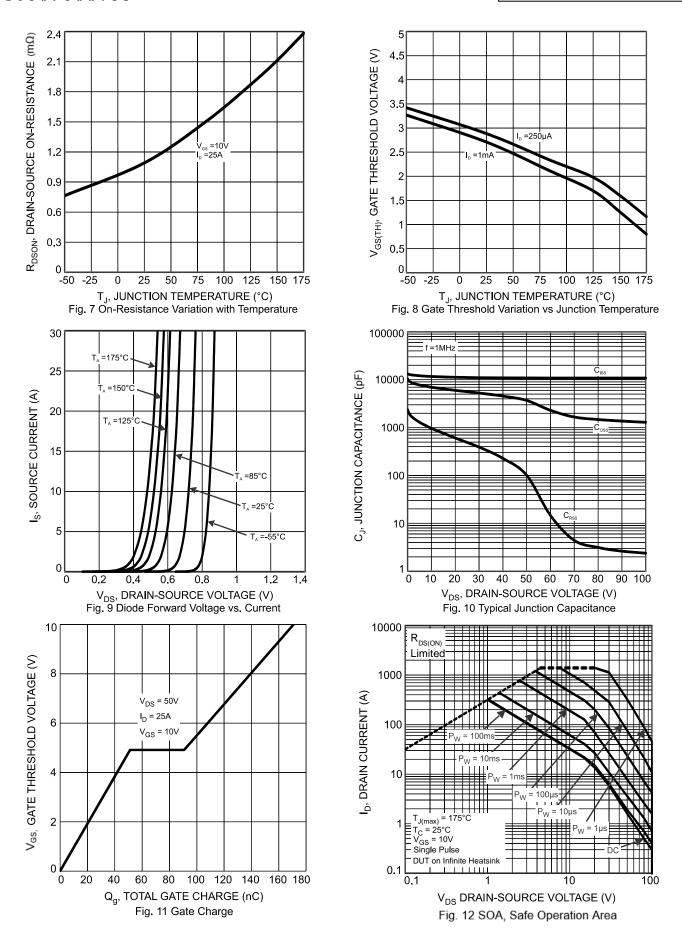


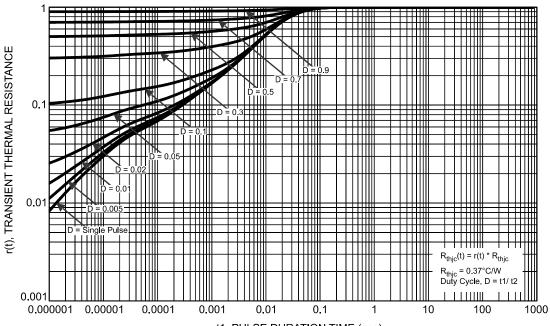
Fig. 6 On-Resistance Variation with Temperature











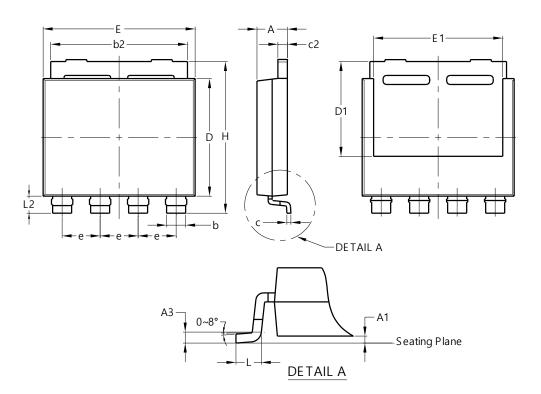
t1, PULSE DURATION TIME (sec) Fig. 13 Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI8080-5

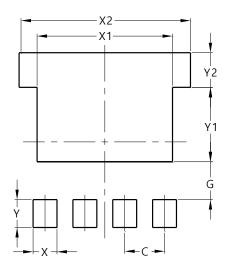


PowerDI8080-5				
Dim	Min	Max	Тур	
Α	1.50	1.70		
A1	0.00	0.15		
A3			0.25	
b	0.90	1.10		
b2	7.10	7.30		
С	0.18	0.24		
c2	0.47	0.57		
D	6.10	6.30		
D1	4.90	5.10		
Е	7.90	8.10		
E1	6.70	6.90		
е			2.00	
Н	7.80	8.10		
L	0.60	0.80		
L2	0.90	1.30		
All Dimensions in mm				

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI8080-5



Dimensions	Value		
	(in mm)		
С	2.00		
G	1.90		
Х	1.20		
X1	6.80		
X2	8.60		
Υ	1.40		
Y1	3.74		
Y2	1.76		



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